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P-Channel 60-V (D-S) MOSFET

Pb-free

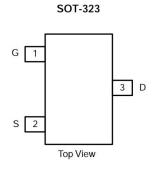
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)	
- 60	170 at V _{GS} = - 10 V	- 1.8	2.8 nC	
	210 at V _{GS} = - 4.5 V	- 1.0	2.0110	

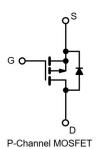
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS tested

APPLICATIONS

- Load Switch
- DC/DC converter





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V _{DS}	- 60	V		
Gate-Source Voltage		V_{GS}	± 20	7		
Continuous Drain Current (T ₁ = 150 °C)	T _C = 25 °C		- 1.8			
Continuous Brain Garrent (1) = 100 °C)	T _C = 70 °C		- 1.6	Α		
Pulsed Drain Current		I _{DM}	- 7.2			
Single-Pulse Avalanche Energy	E _{AS}	2.9	mJ			
	T _C = 25 °C		3.0	W		
Maximum Power Dissipation	T _C = 70 °C	P _D	1.92			
Maximum Fower Dissipation	T _A = 25 °C		1.04 ^{b,c}			
	T _A = 70 °C		0.66 ^{b,c}			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	105	120	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	35	41.6	C/VV	

Notes

- a. $T_C = 25$ °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s
- d. Maximum under steady state conditions is 150 °C/W

Rev. 1. 0



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA	- 60			V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μА	
Zero Gate Voltage Drain Gurrent		V _{DS} = - 48 V, V _{GS} = 0 V, T _J = 55 °C			- 50		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 1.8			Α	
D 1 0 0 0 1 1 2 1 2	D	V _{GS} = - 10 V, I _D = - 1 A		170	200	mΩ	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 1 A		210	280		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 1 A		2.8		S	
Dynamic ^b							
Input Capacitance	C _{iss}			417			
Output Capacitance	C _{oss}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		33		pF	
Reverse Transfer Capacitance	C _{rss}	1		17		1	
Total Gate Charge	Q_g			2.8			
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V, } V_{GS} = -4.5 \text{ V, } I_{D} = -1 \text{ A}$		1		nC	
Gate-Drain Charge	Q_{gd}			1.5			
Gate Resistance	R _g	f = 1 MHz		10		Ω	
Turn-On Delay Time	t _{d(on)}			40			
Rise Time	t _r	$V_{DD} = -30 \text{ V, R}_{L} = 30 \Omega$		25		1	
Turn-Off DelayTime	t _{d(off)}	$I_{D} \cong -1 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_{g} = 1\Omega$		10		ns	
Fall Time	t _f	1		8			
Drain-Source Body Diode Characterist	tics						
Continous Source-Drain Diode Current	Is	T _C = 25 °C			- 1.8	Α	
Pulse Diode Forward Current	I _{SM}				- 7.2		
Body Diode Voltage	V _{SD}	I _S = - 1 A			- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I_ = 1 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		34		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	1 173, αιναι - 100 70μ3, 13 - 23 °C		1.8		nC	

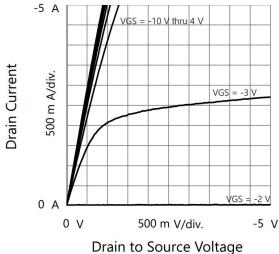
Notes:

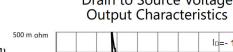
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

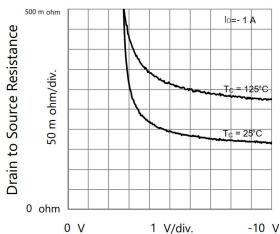
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.



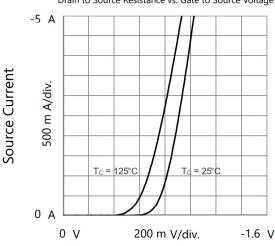
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltage

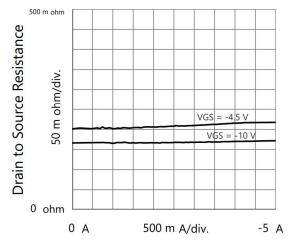


Source to Drain Voltage

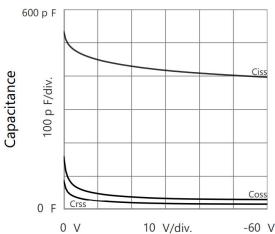
Body Diode Forward Characteristics

-1 A **Drain Current** 100 m A/div. T_C = 25°C 0 A 0 V 500 m V/div. -5 V

Gate to Source Voltage Transfer Characteristics



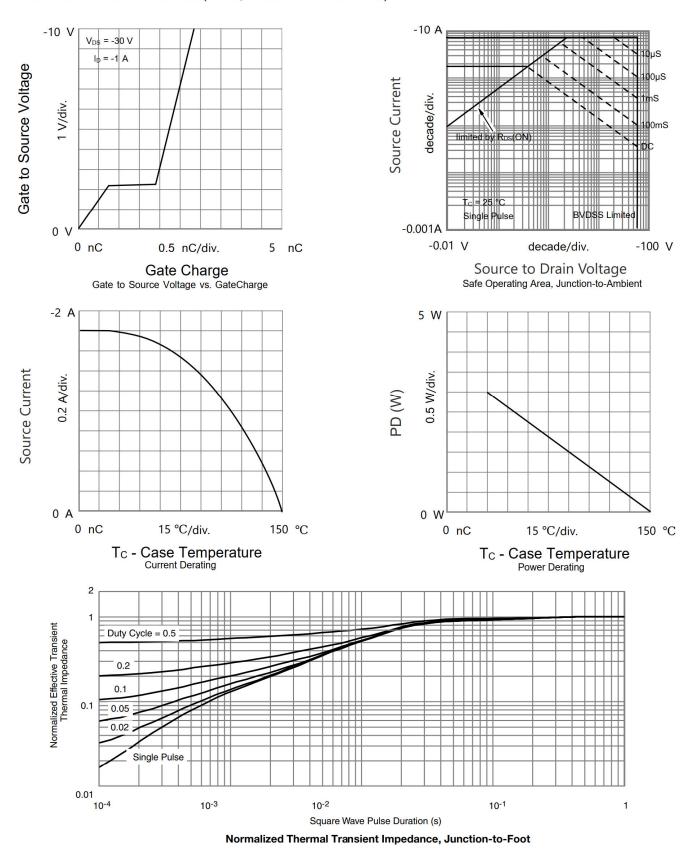
Drain Current Drain to Source Resistance vs. Drain Current



Drain to Source Voltage Capacitances



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





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